

2MBI600VXA-120E-54

IGBT Modules

IGBT MODULE (V series) 1200V / 600A / 2 in one package

■ Features

High speed switching Voltage drive Low Inductance module structure

Applications

Inverter for Motor Drive AC and DC Servo Drive Amplifier Uninterruptible Power Supply Industrial machines, such as Welding machines



Maximum Ratings and Characteristics

Absolute Maximum Ratings (at Tc=25°C unless otherwise specified)

Items	Symbols	Conditions		Maximum ratings	Units
Collector-Emitter voltage	Vces			1200	V
Gate-Emitter voltage	V _{GES}			±20	V
	Ic	Continuous	Tc=25°C	800	
ž		Continuous	Tc=100°C	600	
Collector current	I _{c pulse}	1ms	1ms		Α
드	-I _c				
	-I _{c pulse}	1ms		1200	
Collector power dissipation	Pc	1 device		3350	W
Junction temperature	T _j			175	
Operating junction temperature (under switching conditions)	T _{jop}			150	°C
Case temperature	Tc			150	C
Storage temperature	T _{stg}			-40 ~ +150	
Isolation voltage between terminal and copper base (*1)	V _{iso}	AC : 1min.		4000	VAC
between thermistor and others (*2)	Viso	AC . IIIIII.		4000	VAC
Mounting		M5		6.0	
Screw torque (*3) Main Terminals	rew torque (*3) Main Terminals - M8		10.0	N m	
Sense Terminals		M4		2.1	

Note *1: All terminals should be connected together during the test.

Note *2: Two thermistor terminals should be connected together, other terminals should be connected together and shorted to base plate during the test.

Note *3: Recommendable Value: Mounting 3.0 ~ 6.0 Nm (M5) Recommendable Value: Main Terminals 8.0 ~ 10.0 Nm (M8)

Recommendable Value: Sense Terminals 1.8 ~ 2.1 Nm (M4)

● Electrical characteristics (at Tj= 25°C unless otherwise specified)

4	Comple e la	Conditions	Conditions Characte			ics	Units	
tems	Symbols	Conditions	min.	typ.	max.	Units		
Zero gate voltage collector current	Ices	V _{GE} = 0V, V _{CE} = 1200V		-	-	4.0	mA	
Gate-Emitter leakage current	GES	V _{CE} = 0V, V _{GE} = ±20V		-	-	800	nA	
Gate-Emitter threshold voltage	V _{GE (th)}	V _{CE} = 20V, I _C = 600mA		6.0	6.5	7.0	V	
	V _{CE} (sat)		T _j =25°C	-	1.85	2.30		
	(terminal)		T _j =125°C	-	2.15	-	V	
0 - II t F itt t t It	(*4)	V _{GE} = 15V	T _j =150°C	-	2.20	-		
Collector-Emitter saturation voltage	.,	Ic = 600A	T _i =25°C	-	1.75	2.20		
	V _{CE} (sat)		T _i =125°C	_	2.05	-		
	(chip)		T _i =150°C	-	2.10	-		
Internal gate resistance	Rg _(int)	-		-	1.75	-	Ω	
	Cies	V _{CE} = 10V, V _{GE} = 0V, f = 1	MHz	-	55	-	nF	
	ton	V _{cc} = 600V	-	1000	-	nsec		
Input capacitance	tr	Ic = 600A	-	400	-			
= ' ' ' ' ' '	t _{r (i)}	V _{GE} = ±15V	_	150	-			
	toff	$R_G = 2.4\Omega$		_	1200		-	
Turn-off time	t _f	Ls = 70nH	_	150	_			
	VF		T _i =25°C	-	1.80	2.25		
	(terminal)		T _i =125°C	_	1.95	-	1	
	(*4)	$V_{GE} = 0V$	T _i =150°C	-	1.90	-	i .,	
Forward on voltage	,	I _F = 600A	T _i =25°C	_	1.70	2.15	V	
	VF		T _i =125°C	_	1.85	-	1	
	(chip)			1.80	-	1		
Reverse recovery time	trr	I _F = 600A	1, 200	-	200	-	nsec	
0		T=25°C	,	-	5000	-	Ω	
Resistance B value	R	T=100°C		465	495	520		
B value	В	T=25/50°C	,	3305	3375	3450	K	

Note *4: Please refer to page 7 , there is definition of on-state voltage at terminal.

● Thermal resistance characteristics

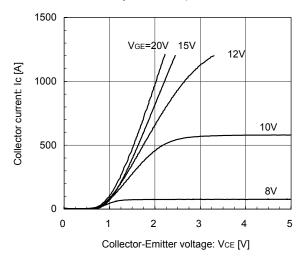
Itomo	Symbols	Conditions	Characteristics			Units
Items	Symbols	ymbols Conditions	min.	typ.	max.	Units
Thermal resistance (1device)	Dth/i a)	Inverter IGBT	-	-	0.045	
	Rth(j-c)	Inverter FWD	-	-	max.	°C/W
Contact thermal resistance (1device) (*5)	Rth(c-f)	with Thermal Compound	-	0.0125	-	

Note $^{*}5$: This is the value which is defined mounting on the additional cooling fin with thermal compound.

■ Characteristics (Representative)

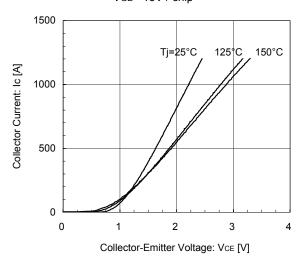
[INVERTER]

Collector current vs. Collector-Emitter voltage (typ.) Tj= 25°C / chip



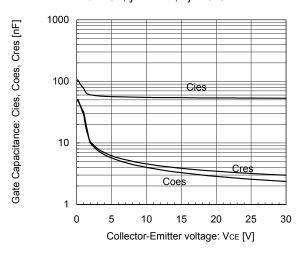
[INVERTER]

Collector current vs. Collector-Emitter voltage (typ.) VGE= 15V / chip



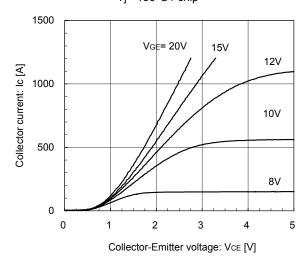
[INVERTER]

Gate Capacitance vs. Collector-Emitter Voltage (typ.) $V_{GE} = 0V, f = 1MHz, Tj = 25^{\circ}C$



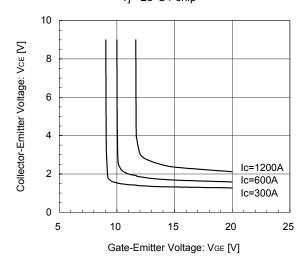
[INVERTER]

Collector current vs. Collector-Emitter voltage (typ.) Ti= 150°C / chip



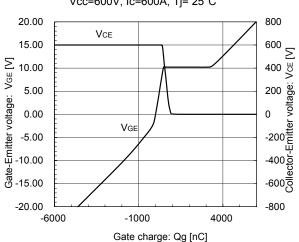
[INVERTER]

Collector-Emitter voltage vs. Gate-Emitter voltage (typ.) Tj= 25°C / chip



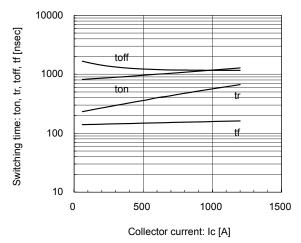
[INVERTER]

Dynamic Gate Charge (typ.) Vcc=600V, Ic=600A, Tj= 25°C



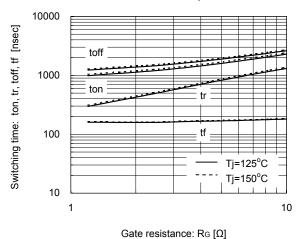
[INVERTER]

Switching time vs. Collector current (typ.) Vcc=600V, VgE= \pm 15V, Rg= 2.4Ω , Tj= 25° C



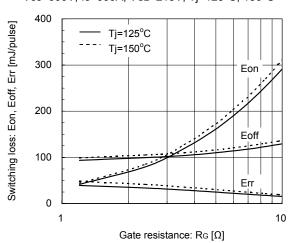
[INVERTER]

Switching time vs. Gate resistance (typ.) Vcc=600V, Ic=600A, VgE=±15V, Tj=125°C, 150°C



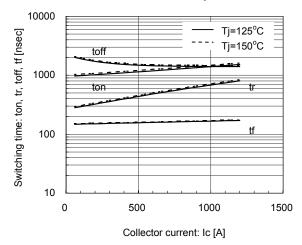
[INVERTER]

Switching loss vs. Gate resistance (typ.) Vcc=600V, Ic=600A, VgE=±15V, Tj=125°C, 150°C



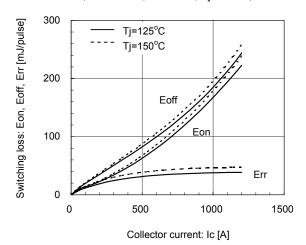
[INVERTER]

Switching time vs. Collector current (typ.) Vcc=600V, VgE= \pm 15V, Rg= 2.4Ω , Tj= 125° C, 150° C



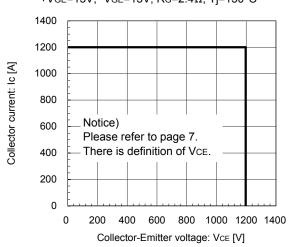
[INVERTER]

Switching loss vs. Collector current (typ.) Vcc=600V , VgE= \pm 15V, Rg=2.4 Ω , Tj=125°C, 150°C

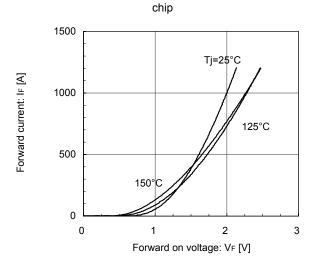


[INVERTER]

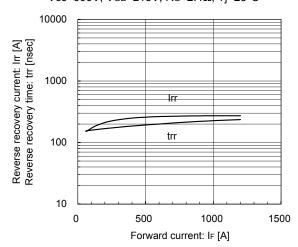
Reverse bias safe operating area (max.) +VgE=15V, -VgE=15V, Rg=2.4 Ω , Tj=150°C



[INVERTER]
Forward Current vs. Forward Voltage (typ.)

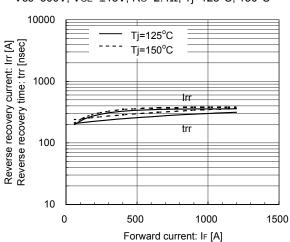


[INVERTER]
Reverse Recovery Characteristics (typ.)
Vcc=600V, VgE=±15V, Rg=2.4Ω, Tj=25°C

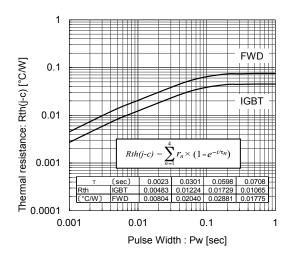


[INVERTER]

Reverse Recovery Characteristics (typ.) Vcc=600V, VgE= \pm 15V, Rg= 2.4Ω , Tj= 125° C, 150° C

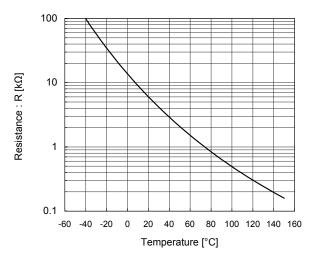


Transient Thermal Resistance (max.)

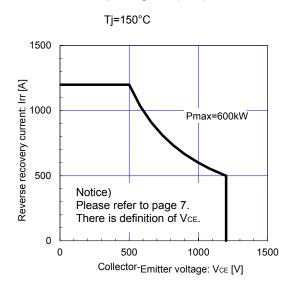


[THERMISTOR]

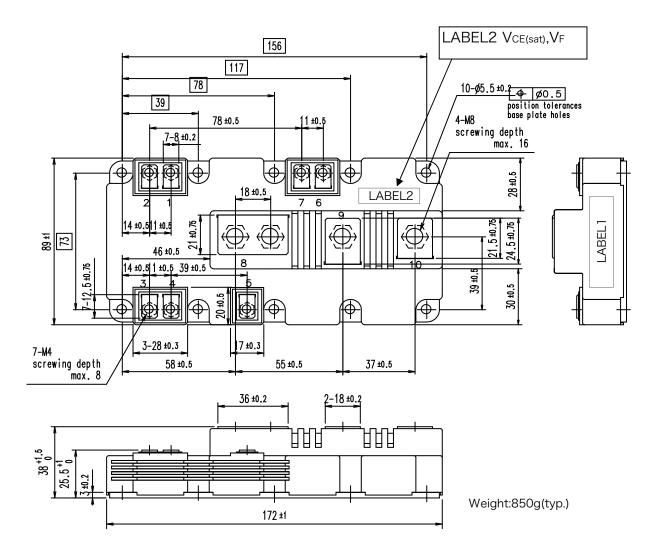
Temperature characteristic (typ.)



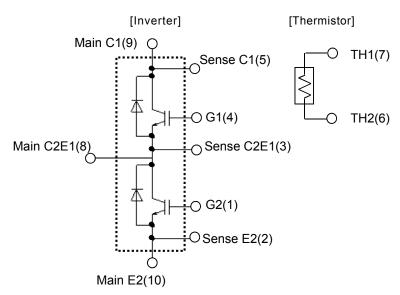
FWD safe operating area (max.)



■ Outline Drawings, mm

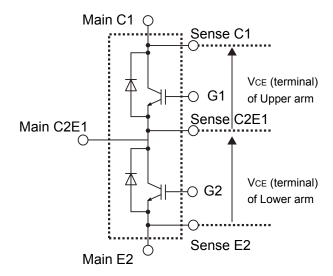


■ Equivalent Circuit Schematic



http://www.fujielectric.com/products/semiconductor/

■ Definition of on-state voltage at terminal and switching characteristics



Fuji defined VcE value of terminal by using Sense C1 and Sense C2E1 for Upper arm and Sense C2E1 and Sense E2 for Lower arm.

Switching characteristics of VcE also is defined between Sense C1 and Sense C2E1 for Upper arm and Sense C2E1 and Sense E2 for Lower arm .

Please use these terminals whenever measure spike voltage and on-state voltage .

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